

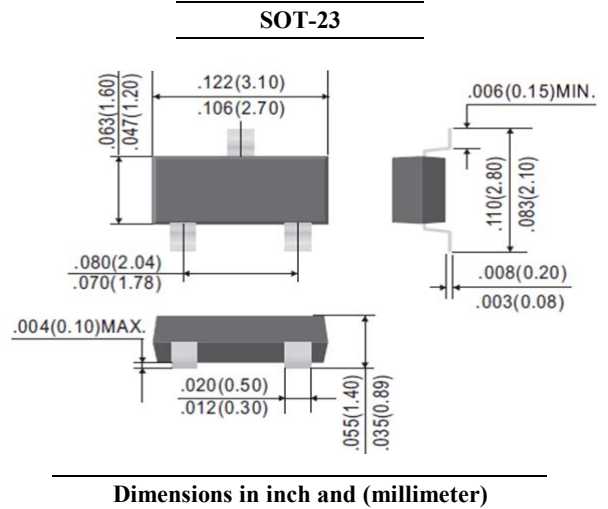
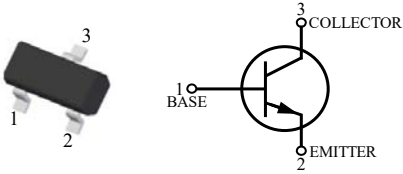


# MMBT5551H

## NPN TRANSISTOR

### FEATURES

- Ideal for medium power amplification and switching
- Suffix "H" indicates Halogen-free parts, ex. MMBT5551H



### Maximum Ratings ( $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	180	V
Collector Emitter Voltage	$V_{CEO}$	160	V
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	600	mA
Power Dissipation	$P_D$	200	mW
Thermal Resistance from Junction to Ambient (Note 1)	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

Note :

1. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

### Electrical Characteristics ( $T_A = 25\text{ }^\circ\text{C}$ unless otherwise specified)

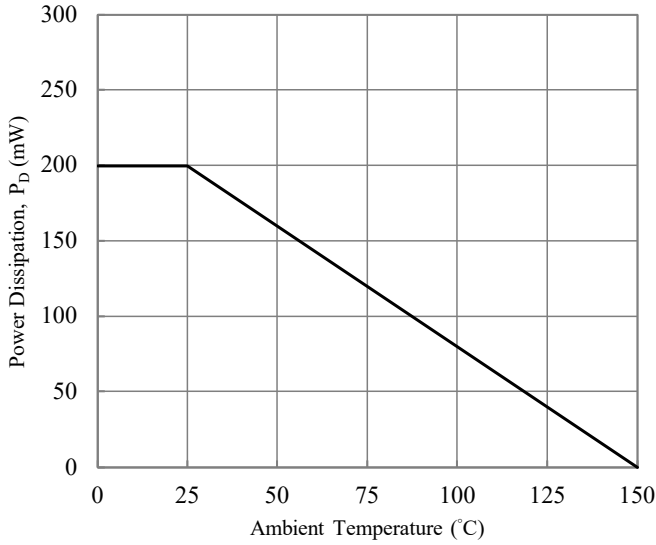
Parameters	Conditions	Symbol	Min.	Max.	Unit
DC Current Gain	$V_{CE}=5\text{V}, I_C=1\text{mA}$	$h_{FE}$	80	-	-
	$V_{CE}=5\text{V}, I_C=10\text{mA}$		80	250	
	$V_{CE}=5\text{V}, I_C=50\text{mA}$		30	-	
Collector Base Breakdown Voltage	$I_C=100\mu\text{A}$	$V_{(BR)CBO}$	180	-	V
Collector Emitter Breakdown Voltage	$I_C=1\text{mA}$	$V_{(BR)CEO}$	160	-	V
Emitter Base Breakdown Voltage	$I_E=10\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Base Cutoff Current	$V_{CB}=120\text{V}$	$I_{CBO}$	-	50	nA
Emitter Base Cutoff Current	$V_{EB}=4\text{V}$	$I_{EBO}$	-	50	nA
Collector Emitter Saturation Voltage	$I_C=10\text{mA}, I_B=1\text{mA}$	$V_{CE(sat)}$	-	0.15	V
	$I_C=50\text{mA}, I_B=5\text{mA}$		-	0.20	
Base Emitter Saturation Voltage	$I_C=10\text{mA}, I_B=1\text{mA}$	$V_{BE(sat)}$	-	1.00	V
	$I_C=50\text{mA}, I_B=5\text{mA}$		-	1.00	
Gain Bandwidth Product	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	$f_T$	100	300	MHz
Collector Base capacitance	$V_{CB}=10\text{V}, f=1\text{MHz}$	$C_{oob}$	-	6	pF



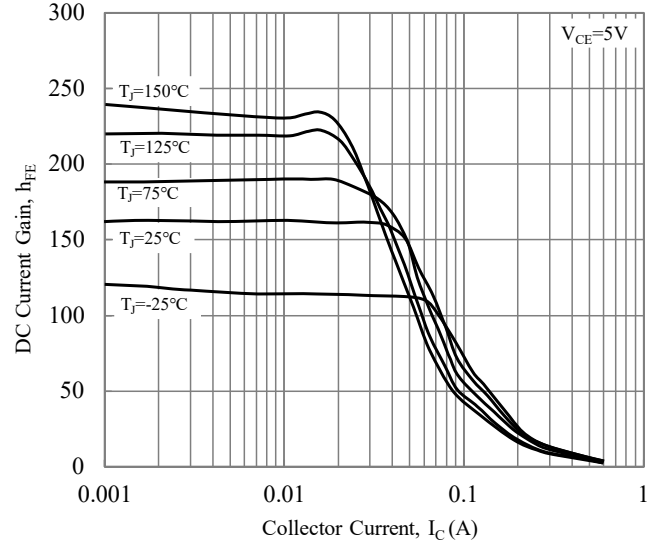
# MMBT5551H

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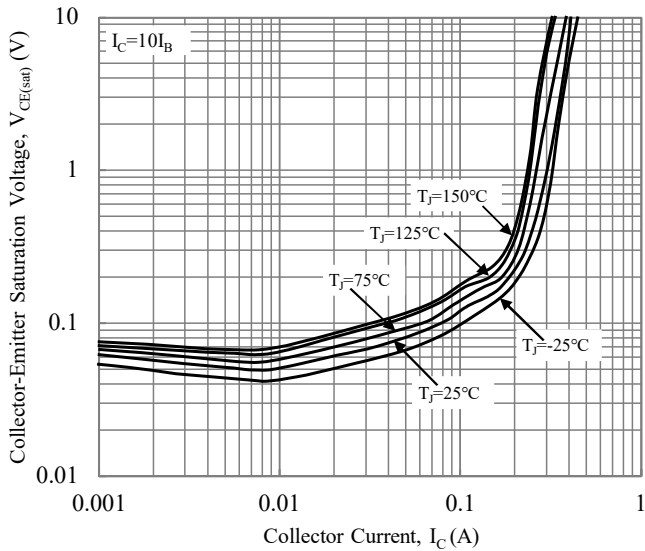
### RATINGS AND CHARACTERISTIC CURVES



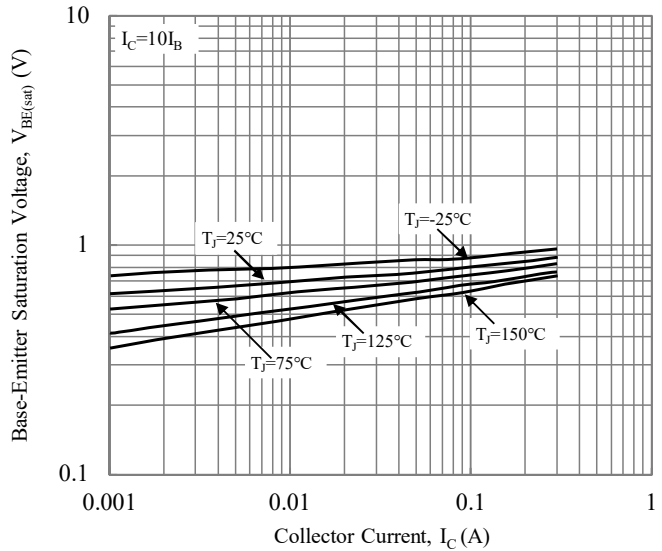
**Fig. 1 Power Derating Curves**



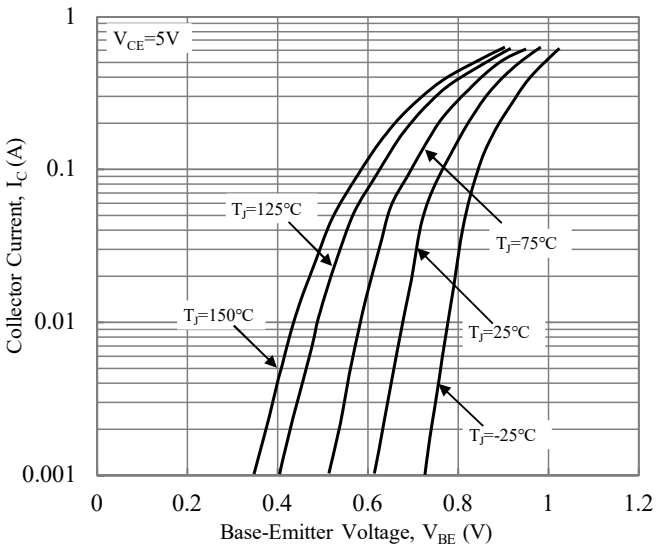
**Fig. 2 Current Gain vs. Collector Current**



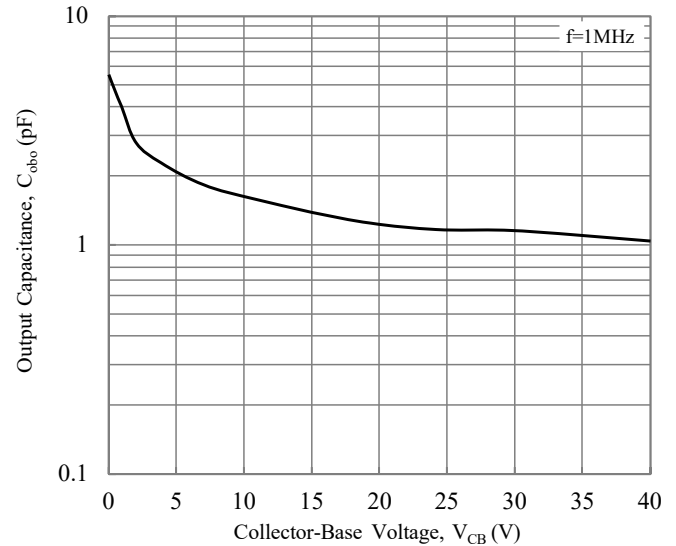
**Fig. 3 Collector-Emitter Saturation Voltage vs. Collector Current**



**Fig. 4 Base-Emitter Saturation Voltage vs. Collector Current**



**Fig. 5 Base-Emitter Voltage vs. Collector Current**

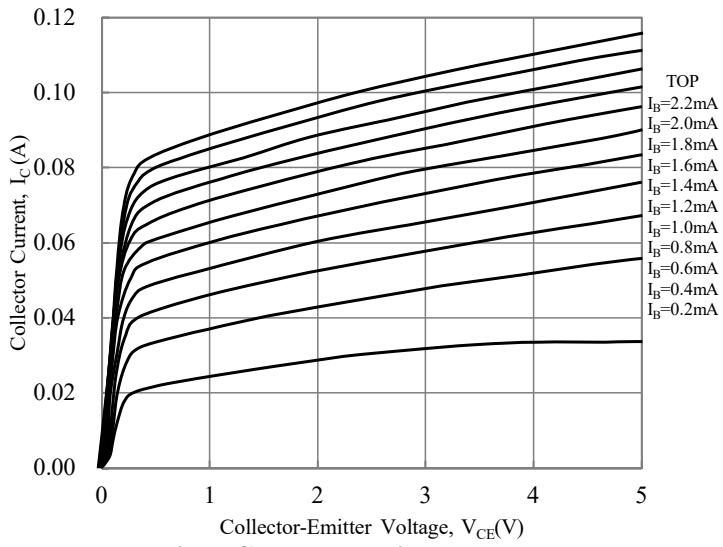


**Fig. 6 Output Capacitance**

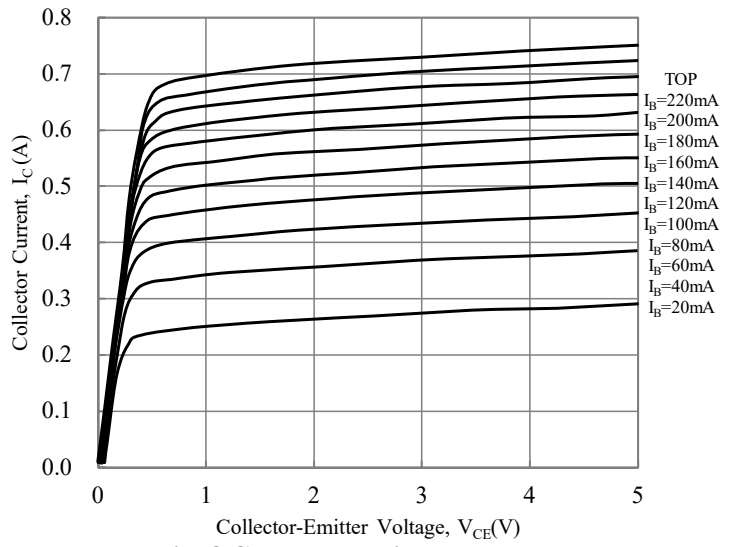


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**Fig. 7 Collector-Emitter Voltage vs. Collector Current**



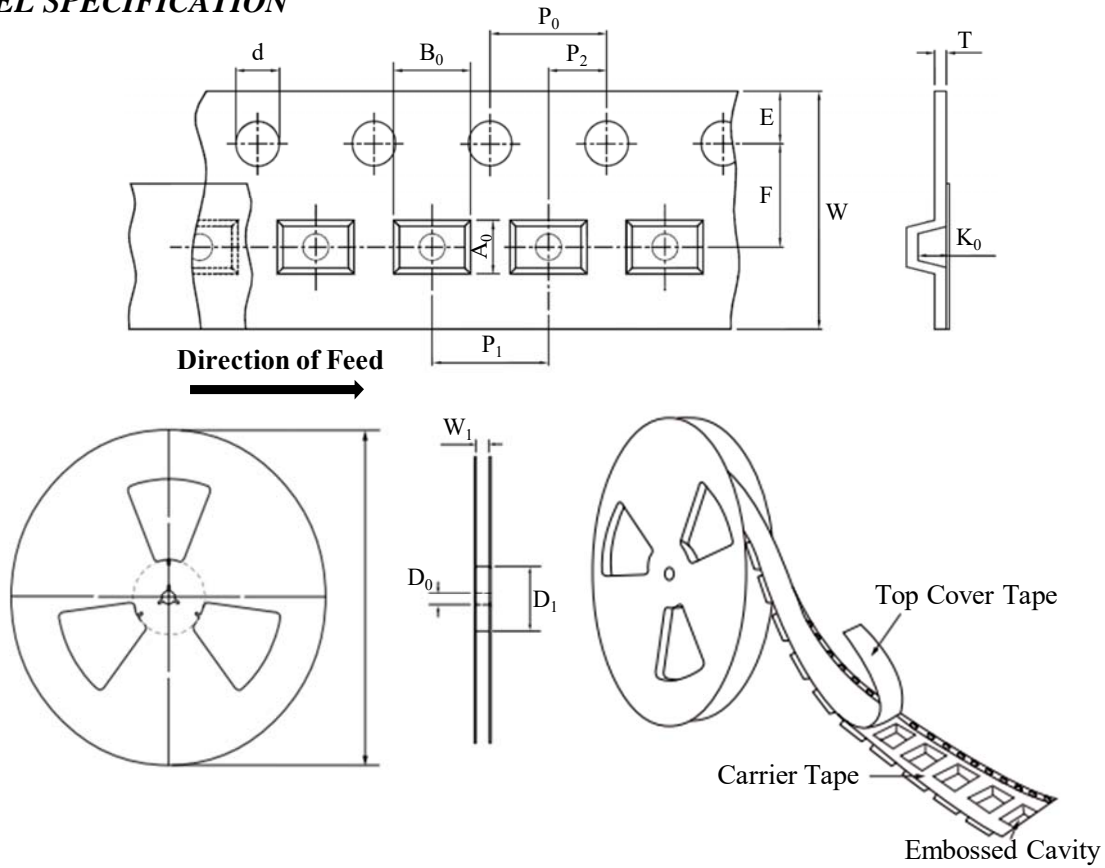
**Fig. 8 Collector-Emitter Voltage vs. Collector Current**



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## NPN TRANSISTOR

### TAPE & REEL SPECIFICATION



Item	Symbol	SOT-23
Carrier width	$A_0$	Note *
Carrier length	$B_0$	
Carrier depth	$K_0$	
Sprocket hole	$d$	$1.50 \pm 0.10$
Reel outside diameter	$D$	$178.00 \pm 2.00$
Feed hole width	$D_0$	$13.00 \pm 0.50$
Reel inner diameter	$D_1$	MIN. 50.00
Sprocket hole position	$E$	$1.75 \pm 0.10$
Punch hole position	$F$	$3.50 \pm 0.10$
Sprocket hole pitch	$P_0$	$4.00 \pm 0.10$
Punch hole pitch	$P_1$	$4.00 \pm 0.10$
Embossment center	$P_2$	$2.00 \pm 0.10$
Overall tape thickness	$T$	$0.20 \pm 0.05$
Tape width	$W$	$8.00 \pm 0.20$
Reel width	$W_1$	MAX. 14.50

Note \*:  $A_0$ ,  $B_0$ , and  $K_0$  are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min. to 0.5 mm max.

### ORDER INFORMATION

Package	Reel Size	Quantity
SOT-23	7"	3,000

### MARKING CODE

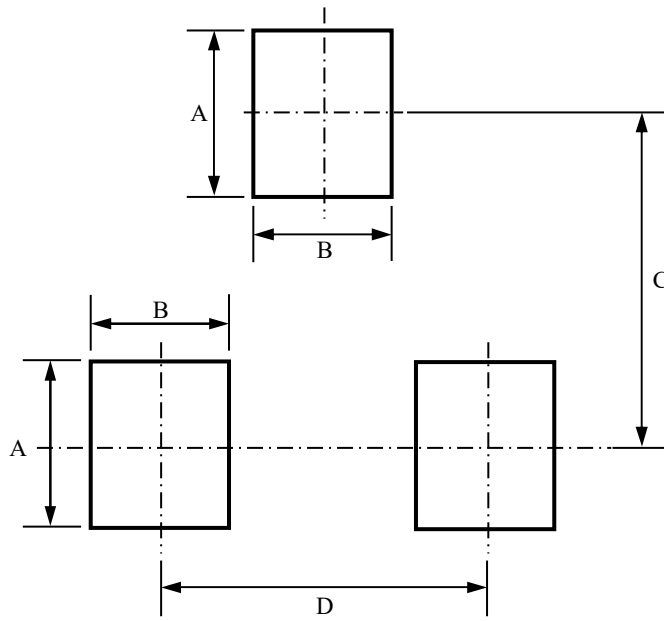
Part Number	Marking Code
MMBT5551H	G1



# MMBT5551H

## NPN TRANSISTOR

### SUGGESTED SOLDER PAD LAYOUT



Unit :mm

PACKAGE	A	B	C	D
SOT-23	1.00	0.80	2.00	1.90